

### FEATURES

- Double Side Cooling
- High Surge Capability

### APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### VOLTAGE RATINGS

| Part and Ordering Number                             | Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$<br>V | Conditions  |
|--|---|---|
| DCR1460F30<br>DCR1460F28<br>DCR1460F26<br>DCR1460F24 | 3000<br>2800<br>2600<br>2400                          | $T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ ,<br>$I_{DRM} = I_{RRM} = 150\text{mA}$ ,<br>$V_{DRM}, V_{RRM} t_p = 10\text{ms}$ ,<br>$V_{DSM}$ & $V_{RSM} =$<br>$V_{DRM}$ & $V_{RRM} + 100\text{V}$<br>respectively |

Lower voltage grades available.

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR1460F30

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### KEY PARAMETERS

|             |                       |
|-------------|-----------------------|
| $V_{DRM}$   | 3000 V                |
| $I_{T(AV)}$ | 1460 A                |
| $I_{TSM}$   | 23000 A               |
| $dV/dt^*$   | 1000 V/ $\mu\text{s}$ |
| $dI/dt$     | 150 A/ $\mu\text{s}$  |

\* Higher  $dV/dt$  selections available

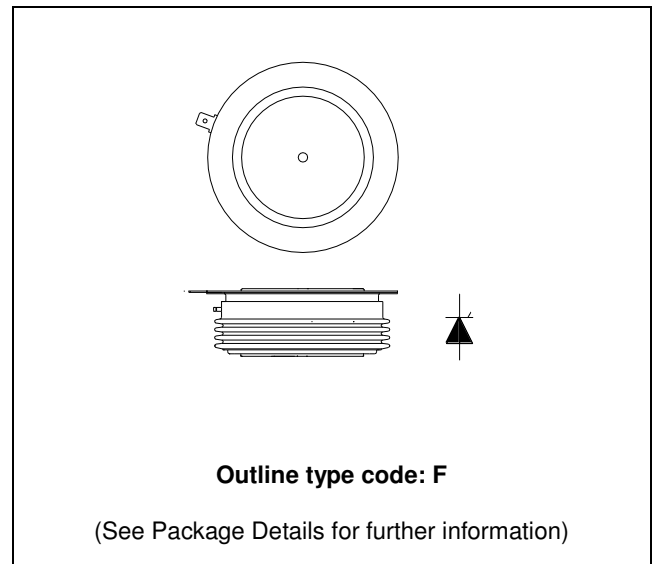


Fig. 1 Package outline

### CURRENT RATINGS

T<sub>case</sub> = 60°C unless stated otherwise

| Symbol                    | Parameter                            | Test Conditions          | Max. | Units |
|---------------------------|--------------------------------------|--------------------------|------|-------|
| <b>Double Side Cooled</b> |                                      |                          |      |       |
| I <sub>T(AV)</sub>        | Mean on-state current                | Half wave resistive load | 1460 | A     |
| I <sub>T(RMS)</sub>       | RMS value                            | -                        | 2290 | A     |
| I <sub>T</sub>            | Continuous (direct) on-state current | -                        | 2060 | A     |

### SURGE RATINGS

| Symbol           | Parameter                               | Test Conditions                           | Max. | Units             |
|------------------|---|---|------|-------------------|
| I <sub>TSM</sub> | Surge (non-repetitive) on-state current | 10ms half sine, T <sub>case</sub> = 125°C | 23.0 | kA                |
| I <sup>2</sup> t | I <sup>2</sup> t for fusing             | V <sub>R</sub> = 0                        | 2.65 | MA <sup>2</sup> s |

### THERMAL AND MECHANICAL RATINGS

| Symbol               | Parameter                             | Test Conditions                              | Min. | Max.  | Units |
|----------------------|---------------------------------------|--|------|-------|-------|
| R <sub>th(j-c)</sub> | Thermal resistance – junction to case | Double side cooled                           | -    | 0.02  | °C/W  |
| R <sub>th(c-h)</sub> | Thermal resistance – case to heatsink | Double side cooled                           | -    | 0.005 | °C/W  |
| T <sub>vj</sub>      | Virtual junction temperature          | Blocking V <sub>DRM</sub> / V <sub>RRM</sub> | -    | 125   | °C    |
| T <sub>stg</sub>     | Storage temperature range             |  | -40  | 140   | °C    |
| F <sub>m</sub>       | Clamping force                        |  | 18   | 26    | kN    |

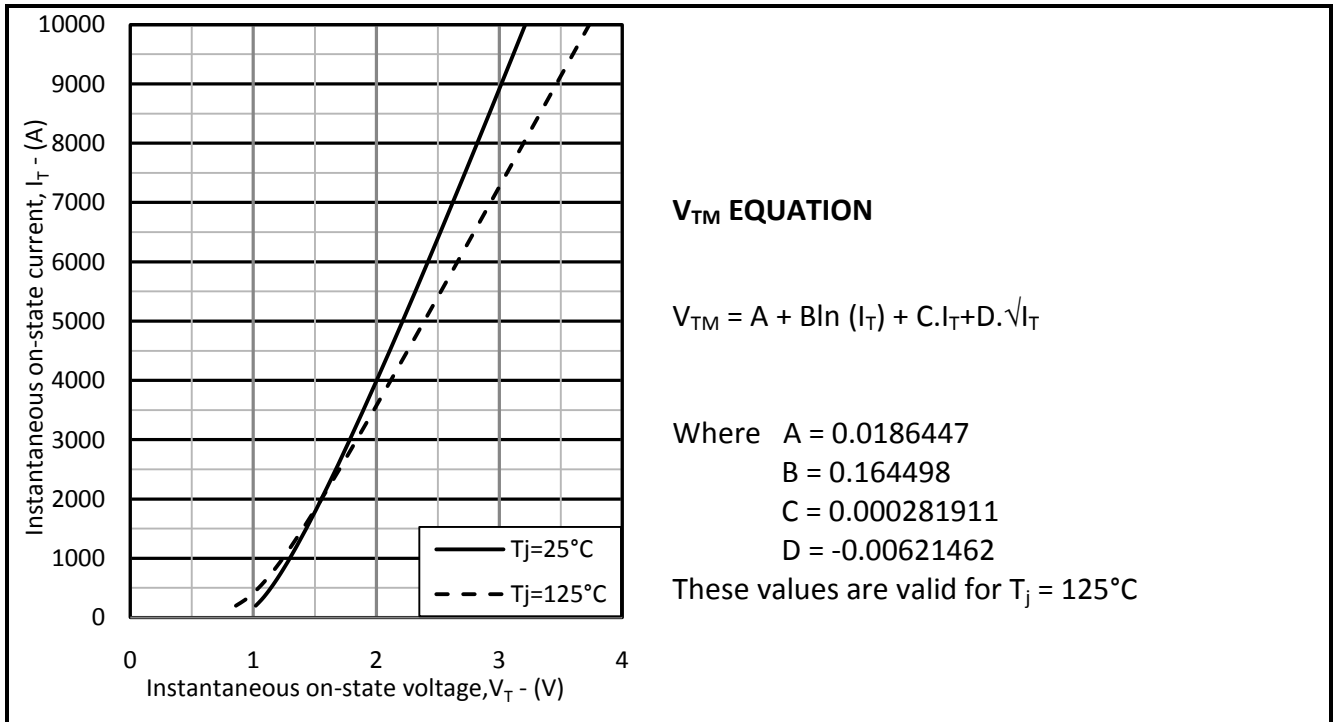
**DYNAMIC CHARACTERISTICS**

| Symbol            | Parameter                                     | Test Conditions   | Min.            | Max. | Units      |            |
|-------------------|---|---|-----------------|------|------------|------------|
| $I_{RRM}/I_{DRM}$ | Peak reverse and off-state current            | At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$  | -               | 150  | mA         |            |
| $dV/dt$           | Max. linear rate of rise of off-state voltage | To 67% $V_{DRM}$ , $T_j = 125^{\circ}C$ , gate open   | 1000            | -    | V/ $\mu s$ |            |
| $di/dt$           | Rate of rise of on-state current              | From 67% $V_{DRM}$ to 2000A<br>Gate source 30V, 10 $\Omega$ ,<br>$t_r < 0.5\mu s$ , $T_j = 125^{\circ}C$        | Repetitive 50Hz | -    | 150        | A/ $\mu s$ |
|                   |   |   | Non-repetitive  | -    | 1000       | A/ $\mu s$ |
| $V_T$             | On-state voltage                              | $I_T = 1500A$ , $T_{case} = 125^{\circ}C$   |                 | 1.40 | V          |            |
| $V_{T(TO)}$       | Threshold voltage                             | $T_{case} = 125^{\circ}C$   | -               | 0.95 | V          |            |
| $r_T$             | On-state slope resistance                     | $T_{case} = 125^{\circ}C$   | -               | 0.30 | m $\Omega$ |            |
| $t_{gd}$          | Delay time                                    | $V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$<br>$t_r = 0.5\mu s$ , $T_j = 25^{\circ}C$                   | -               | 3.0  | $\mu s$    |            |
| $t_q$             | Turn-off time                                 | $T_j = 125^{\circ}C$ , $V_R = 100V$ , $di/dt = 10A/\mu s$ ,<br>$dV_{DR}/dt = 20V/\mu s$ linear to 67% $V_{DRM}$ | -               | 300  | $\mu s$    |            |
| $Q_S$             | Stored charge                                 | $I_T = 2000A$ , $t_p = 1000\mu s$ , $T_j = 125^{\circ}C$ ,<br>$di/dt = 10A/\mu s$ ,                             | -               | 3600 | $\mu C$    |            |
| $I_{RR}$          | Reverse recovery current                      |   | -               | 165  | A          |            |
| $I_L$             | Latching current                              | $T_j = 25^{\circ}C$ ,   | -               | 1    | A          |            |
| $I_H$             | Holding current                               | $T_j = 25^{\circ}C$ ,   | -               | 200  | mA         |            |

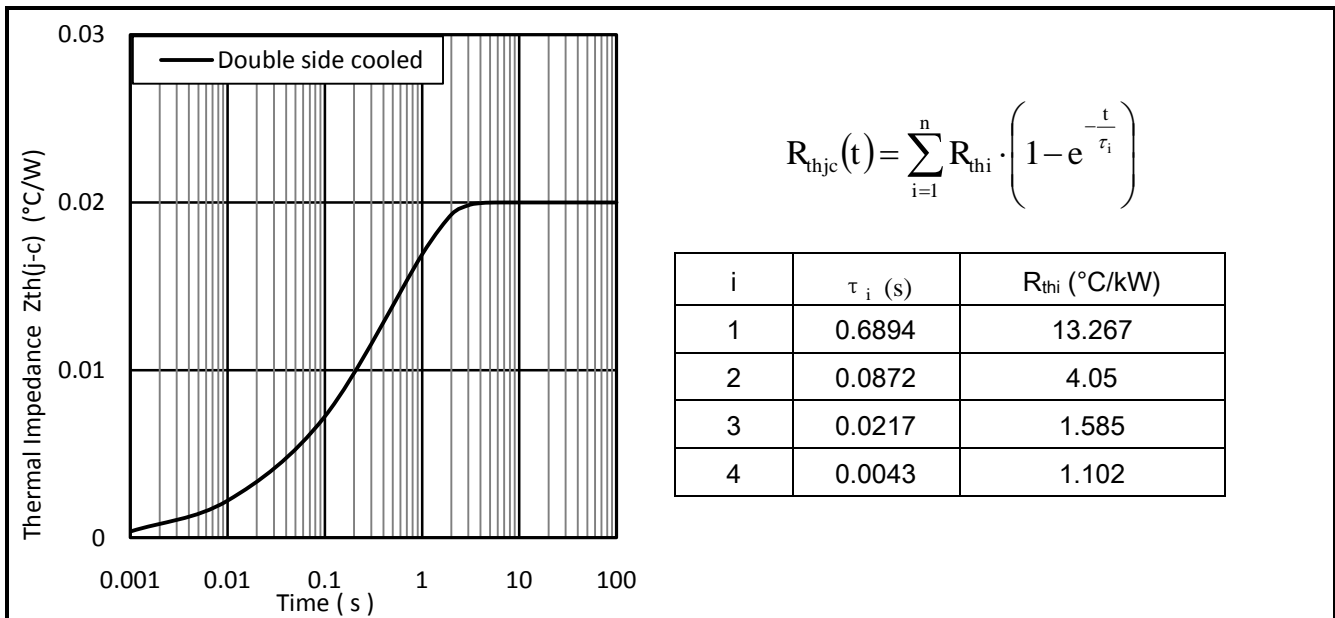
**GATE TRIGGER CHARACTERISTICS AND RATINGS**

| Symbol   | Parameter                | Test Conditions                              | Max. | Units |
|----------|--------------------------|--|------|-------|
| $V_{GT}$ | Gate trigger voltage     | $V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$    | 3    | V     |
| $V_{GD}$ | Gate non-trigger voltage | At 40% $V_{DRM}$ , $T_{case} = 125^{\circ}C$ | TBD  | V     |
| $I_{GT}$ | Gate trigger current     | $V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$    | 300  | mA    |
| $I_{GD}$ | Gate non-trigger current | At 40% $V_{DRM}$ , $T_{case} = 125^{\circ}C$ | TBD  | mA    |

**CURVES**



**Fig.2 Maximum & minimum on-state characteristics**



**Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)**

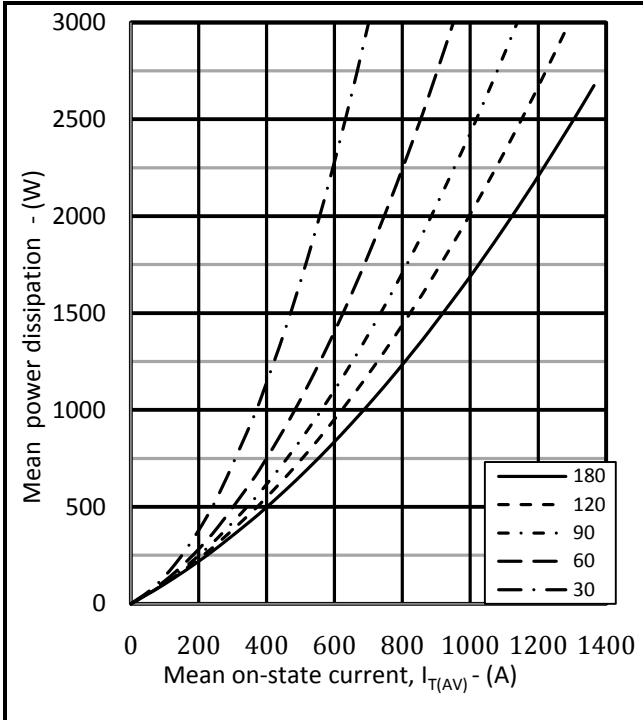


Fig.4 On-state power dissipation – sine wave

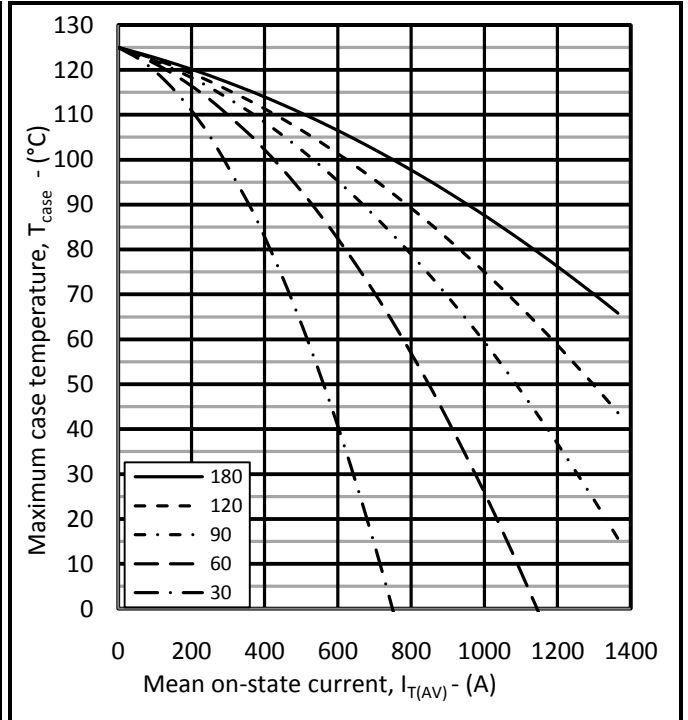


Fig.5 Maximum permissible case temperature, double side cooled – sine wave

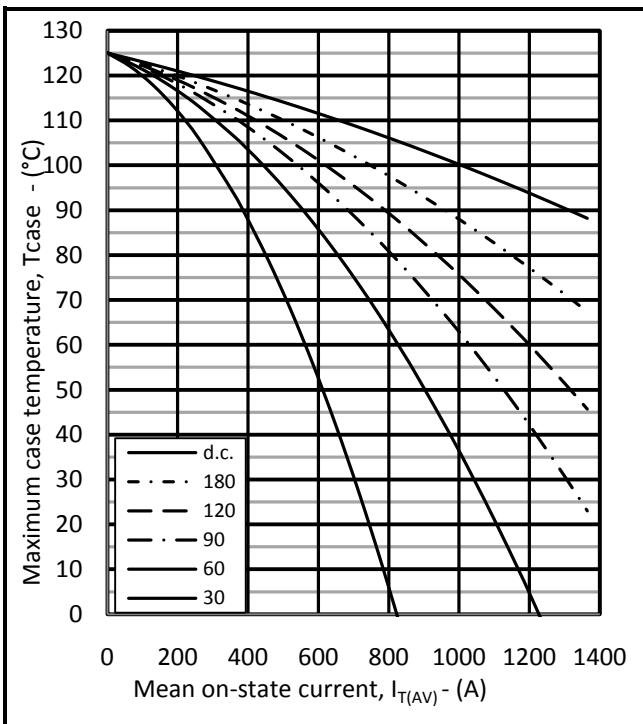


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

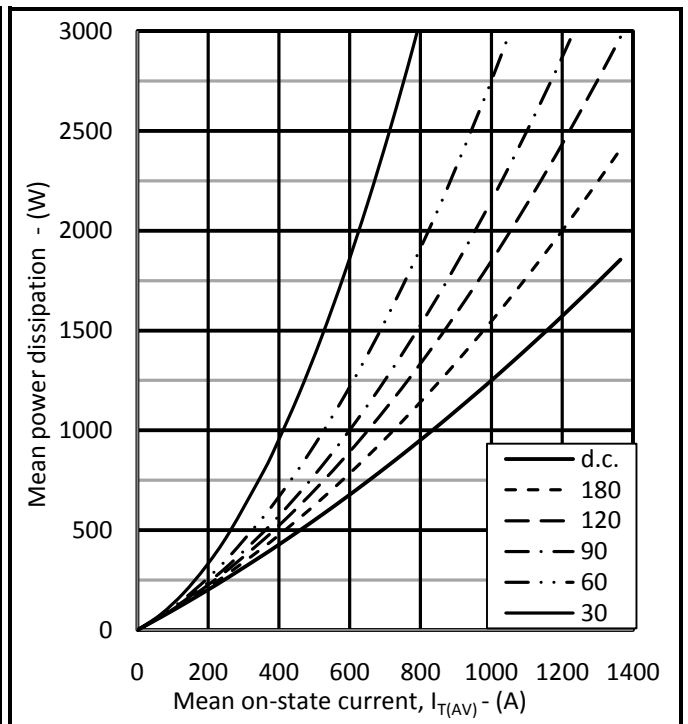


Fig.7 On-state power dissipation – rectangular wave

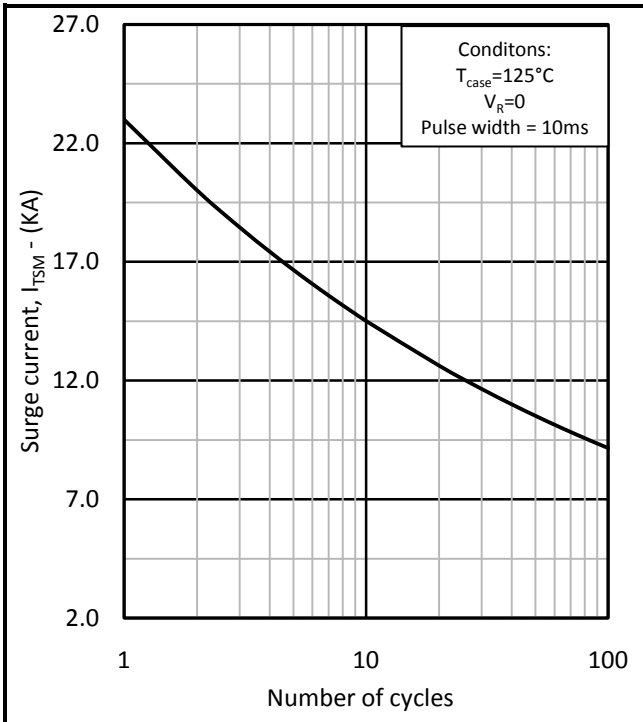


Fig.8 Multi-cycle surge current

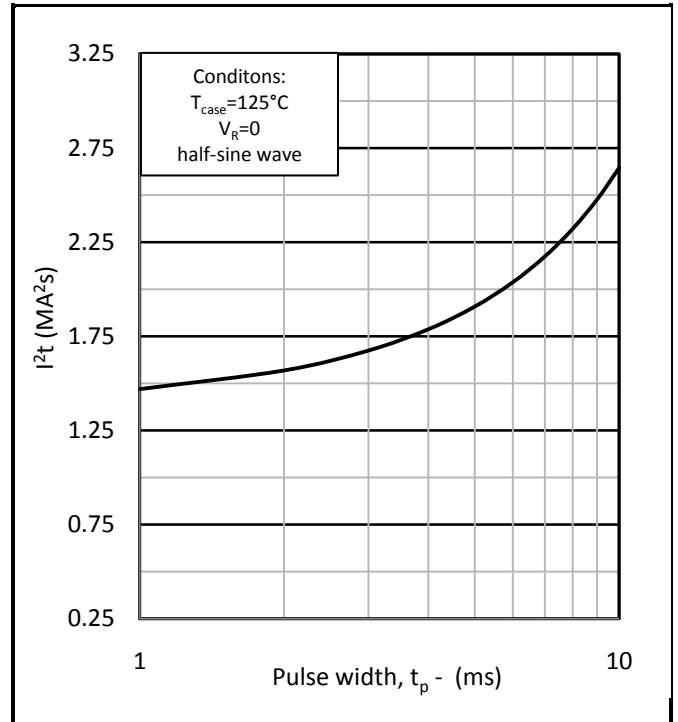


Fig.9 Single-cycle  $I^2t$

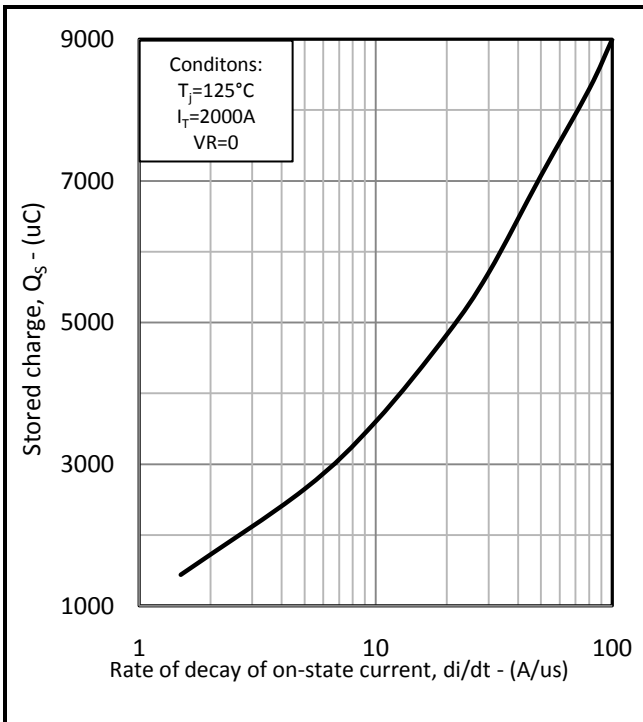


Fig.10 Stored charge vs di/dt

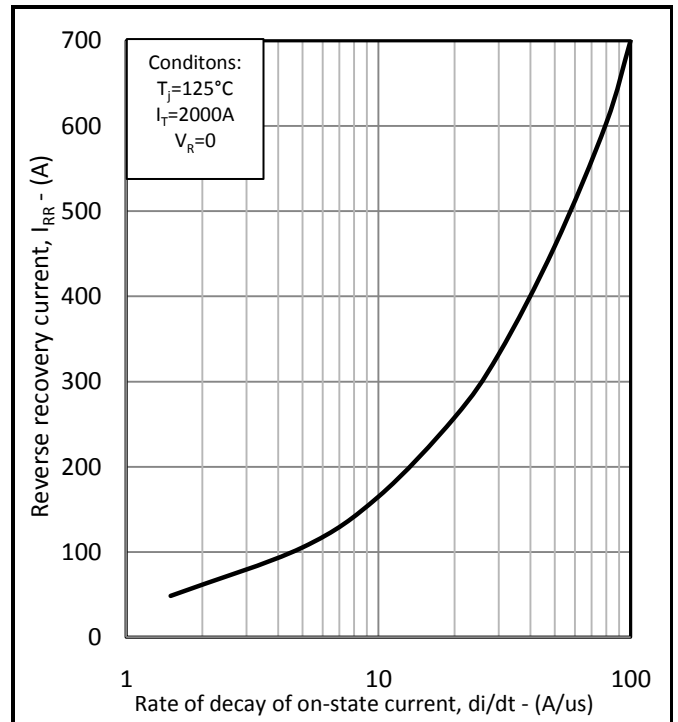


Fig.11 Reverse recovery current vs di/dt

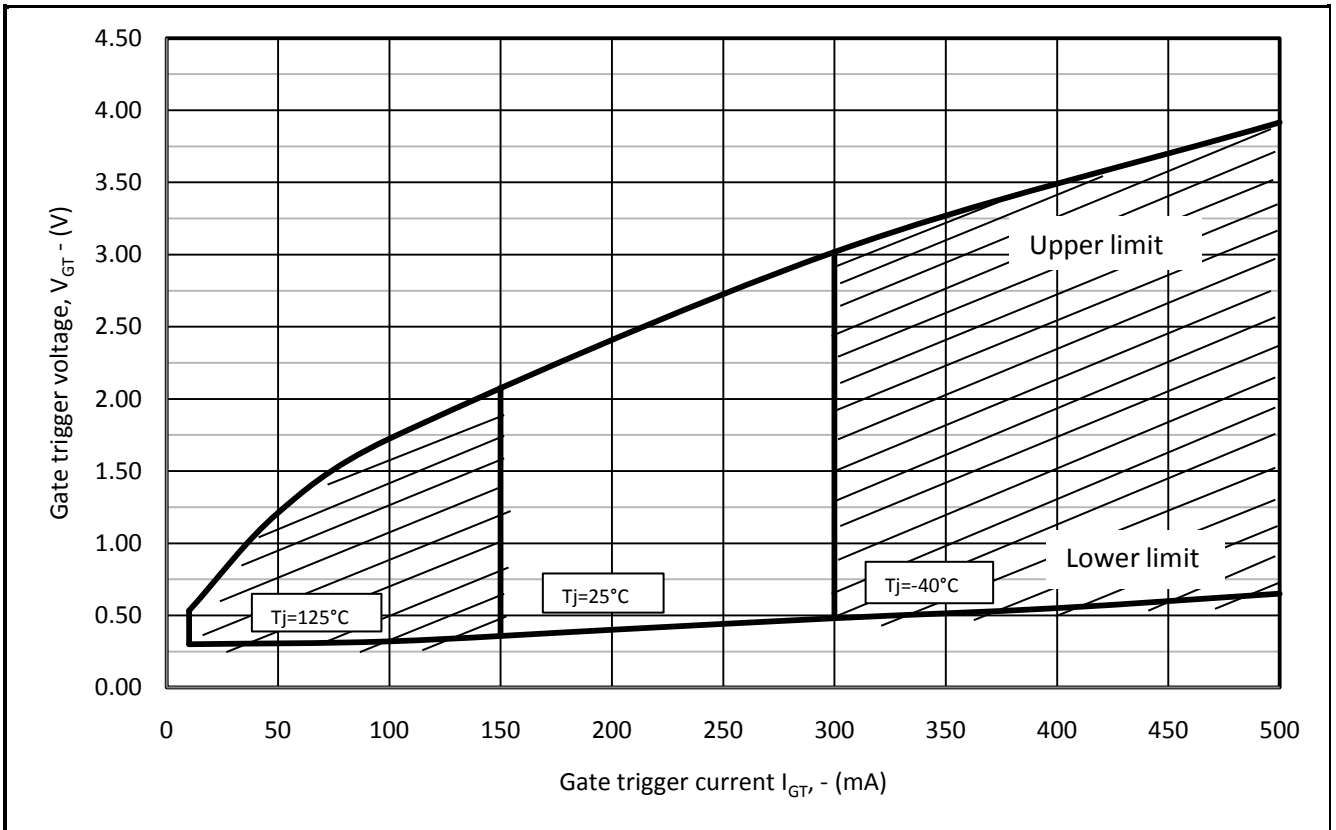
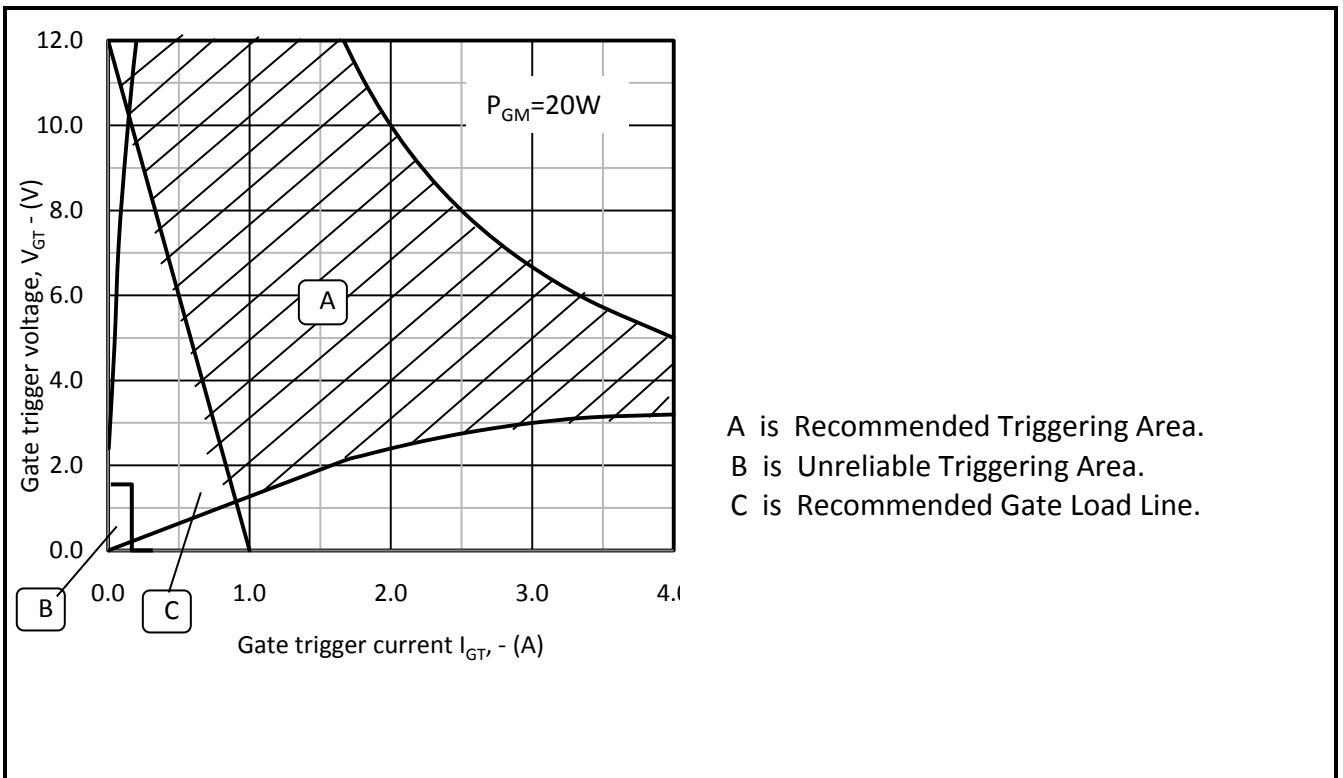


Fig.12 Gate characteristics

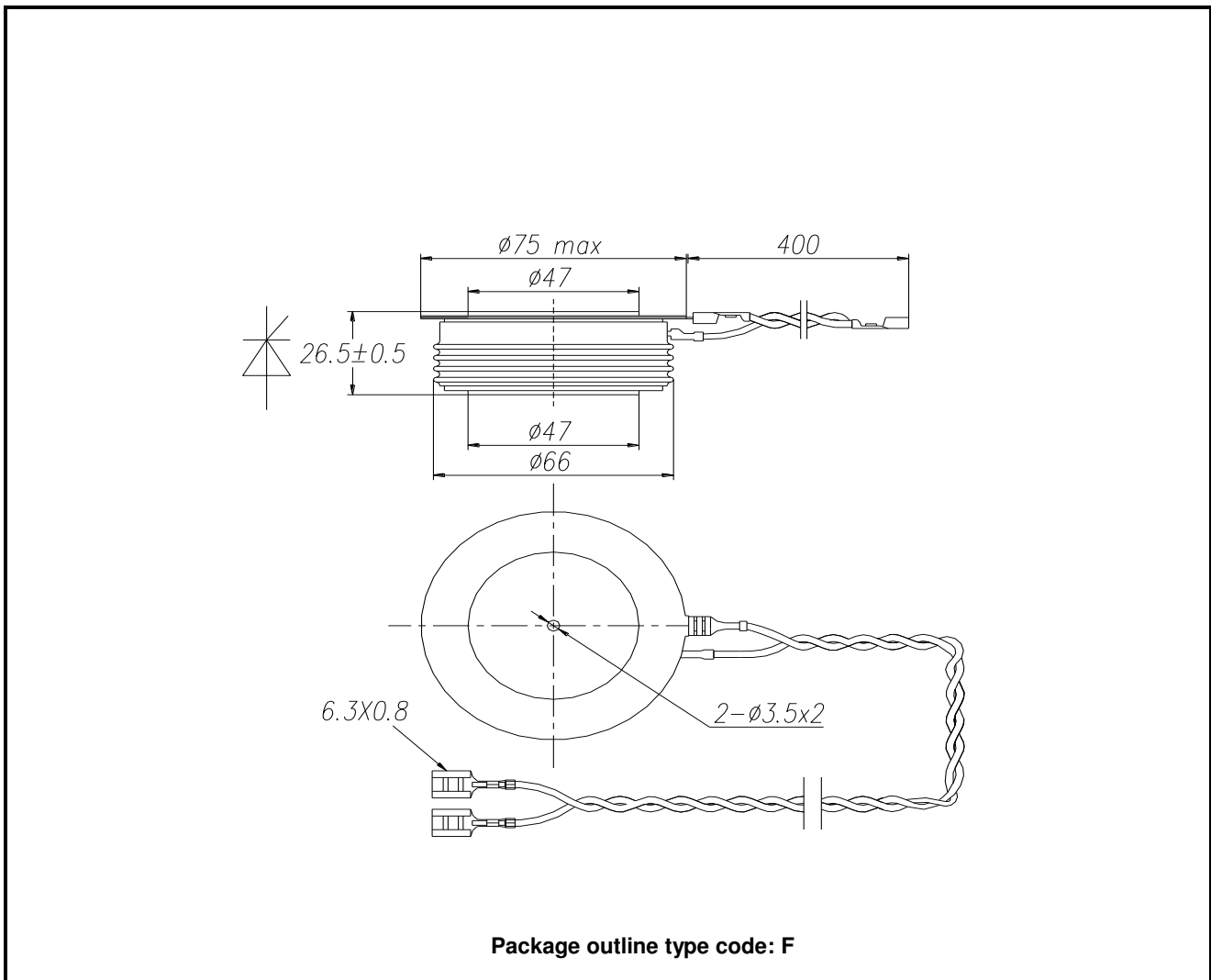


A is Recommended Triggering Area.  
B is Unreliable Triggering Area.  
C is Recommended Gate Load Line.

Fig.13 Gate characteristics

**PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



**Fig.14 Package outline**

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